

V08TC065S1X11

650V GaN Power Switch

Preliminary Datasheet



Description

The D³GaN (Direct Drive D-Mode) V08TC065S1X11 Power Switch integrates a patented, high-density, lateral GaN power transistor, into a **Normally - Off** product with low $R_{DS(on)}$ and exceptionally efficient switching performance.

An **Isolated High Power** SMD package enables applications requiring High Power and Efficiency, with Low Volume and Cost.

The integrated safety function ensure safe operation during system start up and shutdown, while having no impact on the switching performance of the GaN transistor.

Key features

- Ultra-fast switching
- Kelvin connection
- Normally-Off
- Ultra low $R_{DS(on)}$ of 8m Ω
- Fully isolated package (3.5KV)
- High Threshold Voltage >5V
- Driven by standard 15V driver
- Top cooling package

Applications

- Automotive
- AC motors
- Solar Inverter
- AC-DC Power Supply
- Battery chargers
- Laser driver

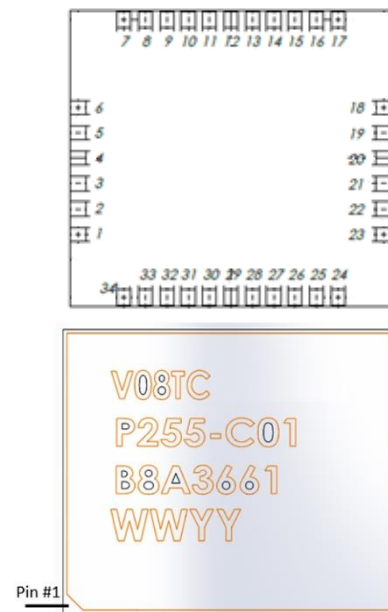


Fig. 1: Die Pinout

Key Performance Parameters

Parameter	Value	Units
V_{DS}	650	V
$R_{DS(on)}$	8	m Ω
Q_G	110	nC
$I_{D,pulse}$	380	A
I_D	200	A

Pin	Function
24-34	Source
1, 22	Activation signal
3, 21	Com signal
4, 20	Gate
2, 23	Com power
7-17	Drain
5, 6, 18, 19	NC*

*Do not connect to any signal

Ordering Information:

Part Number	Packing	Marking	Ordering Number
V08TC065S1X11	Tray	V08TC065S1X11	V08TC065S1X11T

Maximum ratings (Tc =25°C unless otherwise specified)					
Parameter	Symbol	Min	Max	Unit	Conditions
Drain-Source breakdown voltage	$V_{(BR)DS}$	650	-	-	
Drain Source Transient voltage	$V_{DS(transient)}$		800	V	Pulse $\leq 1\mu s$
Continuous Drain current ¹⁾	I_D	-	200	A	$T_C = 100^\circ C^{1)}$
			170		
Pulsed Drain current ²⁾	$I_{D,pulse}$	-	450	A	
Gate Source voltage	V_{GS}	-20	0	V	Pin4, 20 to pin2, 23
Transient Gate Source voltage	$V_{GS(transient)}$	-25	6	V	Pulse $\leq 1\mu s$
Power dissipation	P_{TOT}	-	500	W	
Operating and storage temperature	T_j, T_{stg}	-55	+150	$^\circ C$	
Continuous reverse current	I_s	-	200	A	$T_C = 25^\circ C^{1)}$
Reverse pulse current ¹⁾	$I_{s,pulse}$	-	380	A	
Gate leakage	I_{gss}	-	200	μA	$V_{DS} = 650V,$ $V_{GS} = -15V$
Thermal Characteristics					
Thermal resistance, junction-case	$R_{\theta JC}$	-	0.1	$^\circ C/W$	
Thermal resistance, junction - ambient	$R_{\theta JA}$	-	65	$^\circ C/W$	
Soldering peak body temperature	T_p	-	260	$^\circ C$	
Time within 5°C from peak soldering temperature	t_c	-	30	S	

- 1) Limited by Tj max of 150°C, Vgs = 0V, considering Rth(JC) in a discrete package = 0.1°C/W
2) Duty cycle =10% and pulse width limited by Tjmax.

Electrical characteristics ($T_J = 25^\circ\text{C}$, $V_{GS} = -15\text{V}$ unless otherwise specified)						
Parameter	Symbol	Min	Typical	Max	Unit	Conditions
Static						
Gate threshold voltage ¹	V_{th}	5	5.5	6	V	$I_D = 47\text{mA}$, $V_{DS} = 10\text{V}$
Recommended driving voltage ²	V_{DD}		15		V	Refer to driver GND
Drain Source leakage current	I_{DSS}	-	30	60	μA	$V_{DS} = 650\text{V}$
		-	75	200		$V_{DS} = 650\text{V}$ $T_J = 150^\circ\text{C}$
Gate resistance	R_G	-	0.5	-	Ω	$f = 1\text{MHz}$
Drain-Source on state resistance	$R_{DS(ON)}$	-	8	12	$\text{m}\Omega$	$V_{GS} = 0\text{V}$ $I_D = 35\text{A}$
		-	17.5	-		$V_{GS} = 0\text{V}$ $I_D = 35\text{A}$ $T_J = 150^\circ\text{C}$
Reverse voltage drop- GaN non conductive	V_R	-	-	7.5	V	$I_D = 10\text{A}$
		-	-	9.5		$I_D = 10\text{A}$ $T_J = 150^\circ\text{C}$
Reverse voltage drop- GaN conductive	V_R	-	-	0.08	V	$I_D = 10\text{A}$, $V_{GS} = 0\text{V}$
		-	-	0.16		$I_D = 10\text{A}$, $T_J = 150^\circ\text{C}$ $V_{GS} = 0\text{V}$
Reverse recovery time	t_{rr}	-	-	0	ns	
Reverse recovery charge	Q_{rr}	-	-	0	nC	
Output Charge	Q_{oss}	-	-	420	nC	$V_{DS} = 400\text{V}$
Dynamic						
Input capacitance	C_{iss}	-	2000	2200	pF	$f = 1\text{MHz}$ $V_{DS} = 400\text{V}$
Output capacitance	C_{oss}	-	500	600		
Reverse transfer capacitance	C_{rss}	-	70	100		
Effective Output Capacitance, Energy Related	$C_{O(ER)}$	-	-	1100	pF	$V_{DS} = 0-400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	13.5	-	ns	$V_{DS} = 400\text{V}$, $V_{DD} = 15\text{V}^1$ $I_D = 35\text{A}$, BJT Gate Buffer $R_{base} = 100\Omega$ for ON & 20Ω for OFF
Fall time	t_f	-	22	-		
Turn-off delay time	$t_{d(off)}$	-	8.1	-		
Rise time	t_r	-	10.5	-		

- 1) Refers to driver GND, see typical operating circuit. Threshold voltage defined as $V_{th} = V_{DD} + V_{th-GaN} = 15\text{V} + [-9]\text{V} = 6\text{V}$
2) In operation V_{gs} swings from $-V_{DD}$ (OFF state) to 0V (ON state).

Electrical characteristics (T _J =25°C unless otherwise specified)						
Parameter	Symbol	Min	Typical	Max	Unit	Conditions
Gate Charge characteristics						
Gate to Source charge	Q _{GS}	-	8	-	nC	V _{GS} =0V to -14V V _{DS} =400V I _D =32A
Gate to Drain charge	Q _{GD}	-	130	-		
Total Gate charge	Q _G	-	200	-		

Pin Characteristics						
Parameter	Symbol	Min	Typical	Max	Unit	Conditions
Pin 1, 22 Activation signal ²⁾						
Disable voltage	Pin 1, 22	0	-	9.1	V	
Enable voltage	Pin 1, 22	9.3	15	15		
Absolute maximum rating ³⁾	Pin 1, 22	-20	-	10		
Pin 3, 21 Com signal ³⁾						
Voltage at Disable mode	Pin 3, 21	-	8	-	V	VDS >20V
Voltage at Enable mode	Pin 3, 21	0	0	0.1		
Pin 2, 23 Com Power ²⁾						
	Pin 2, 23	10	15	20	V	
Pin 5 Enable must be connected to pin 1 or 22						

- 1) After applying Activation signal
- 2) Refers to driver GND, see typical operating circuit
- 3) Refers to Source Pins

Typical Characteristics at 25C° (unless noted otherwise)

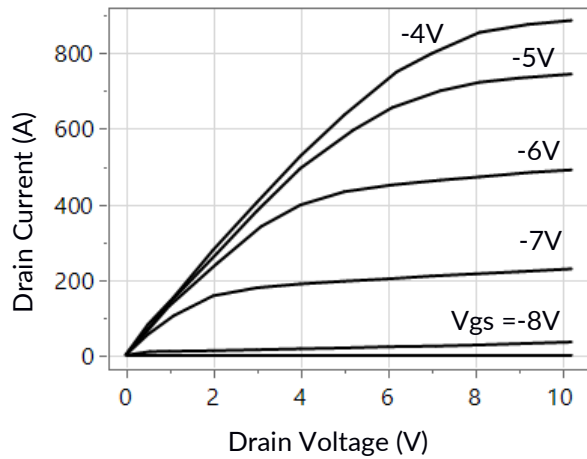


Figure 1 Output (Forward) Characteristics

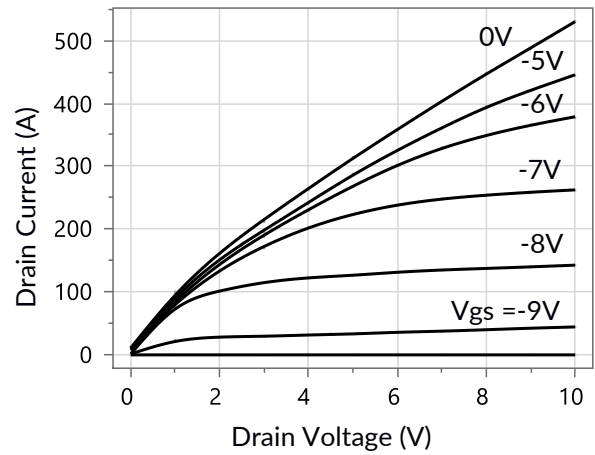


Figure 2 Output (Forward) Characteristics
Tj=150C

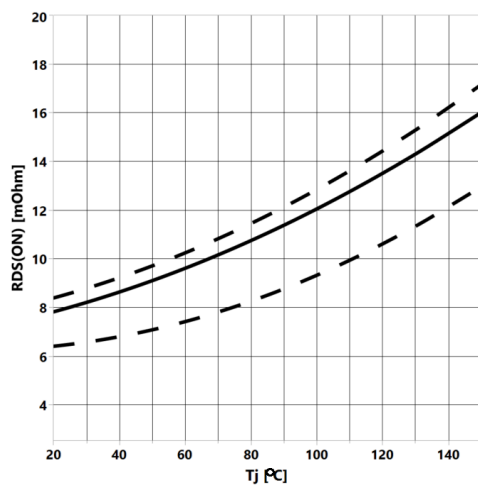


Figure 3 ON-State Resistance vs. Temperature

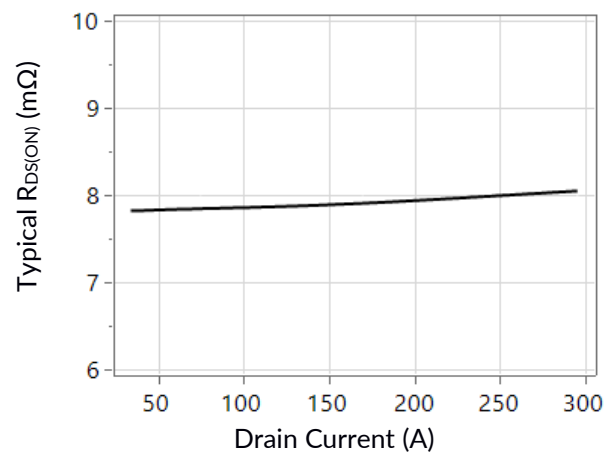


Figure 4 ON-State Resistance vs. Current at
25°C

Typical Characteristics cont.

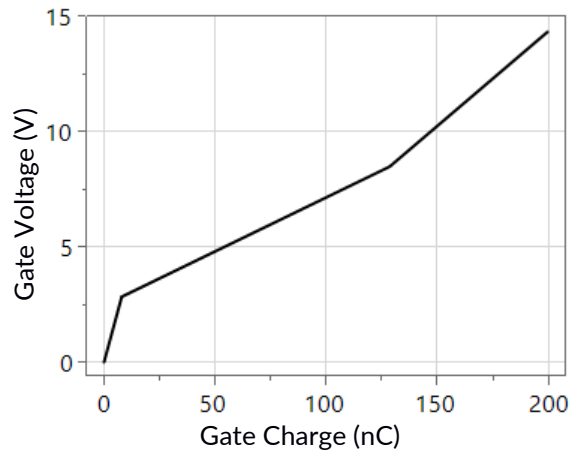


Figure 5 Typical Gate Charge

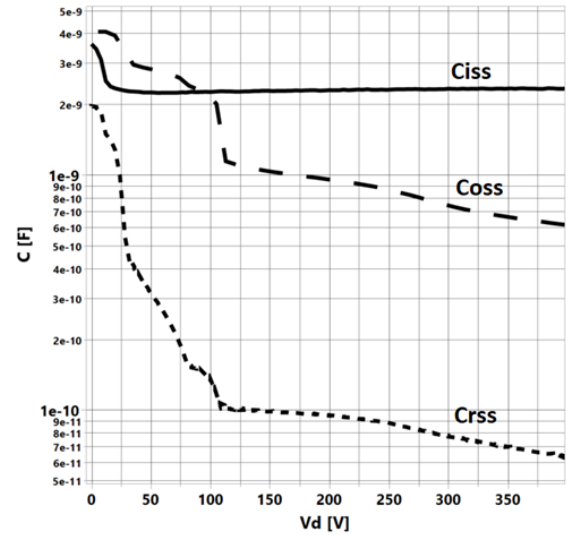


Figure 6 Typical Capacitances

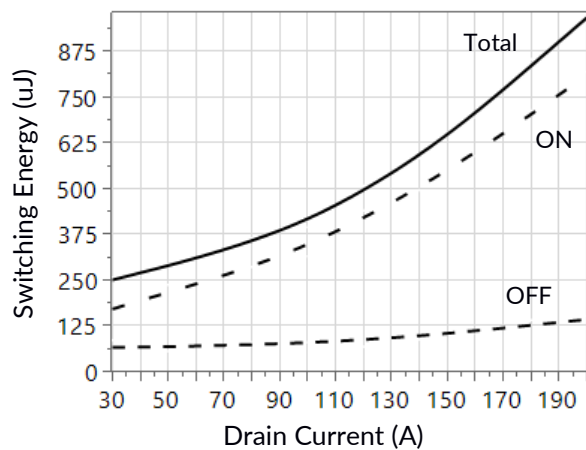


Figure 7 Typical Switching Energy vs Drain Current at 400V

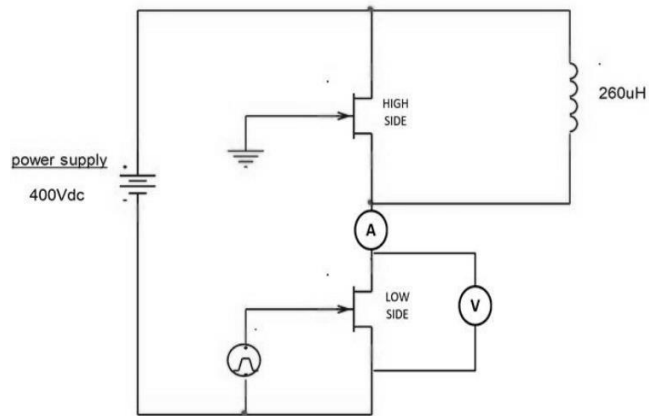


Fig.16: Switching parameters test circuit

Switching Time Waveforms

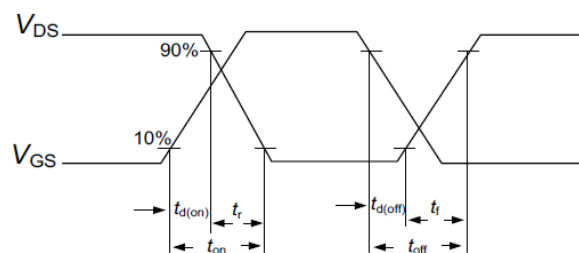
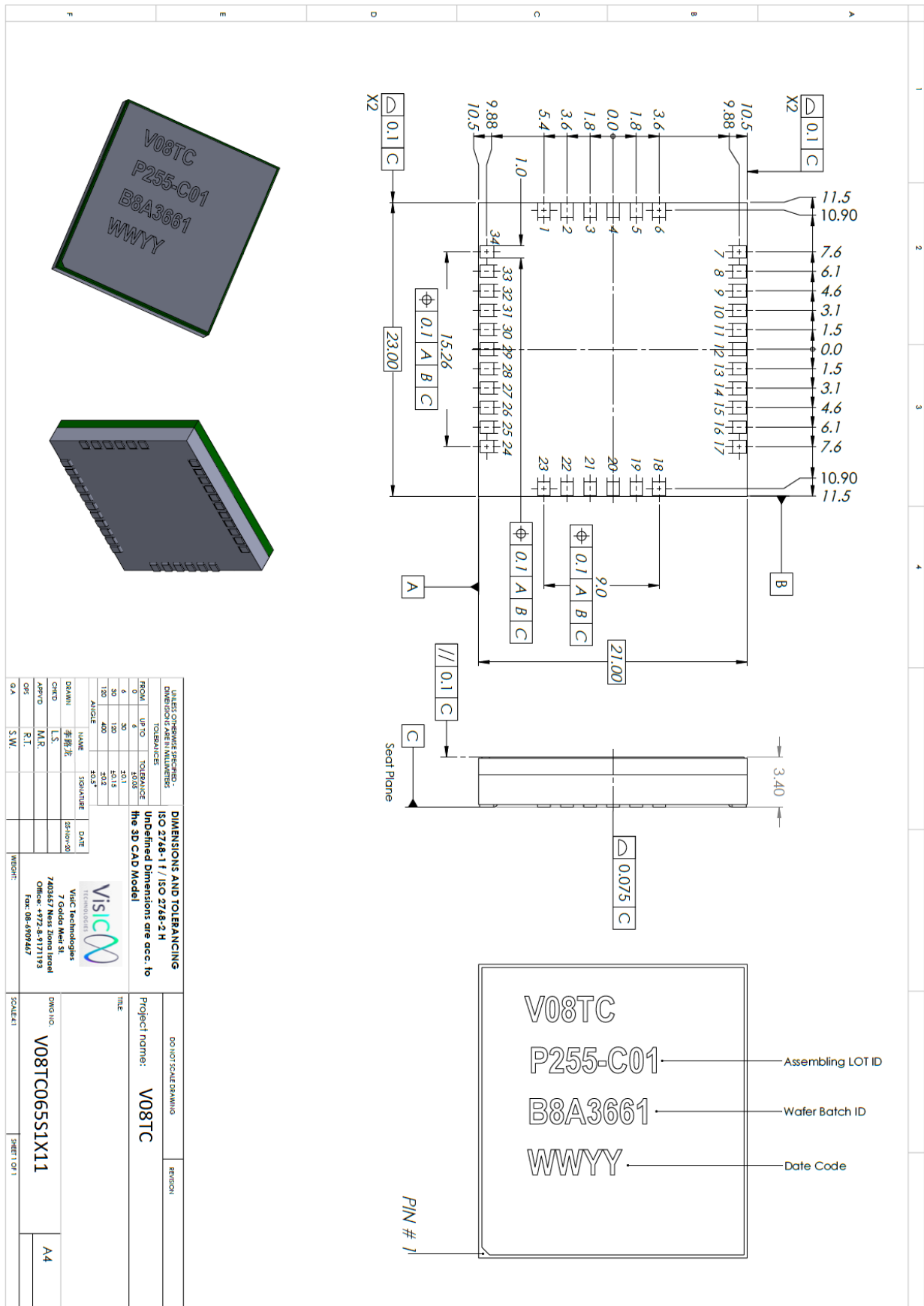


Fig.17: Switching time waveforms

Package Outlines:



Rev.	Date	Content of Change	Owner
1.0	31/07/2023	New datasheet and template under new part number	I.B
1.1	22/08/2023	Changed Rdson value slightly based on updated die measurements, revised Pin characteristics table.	I.B

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